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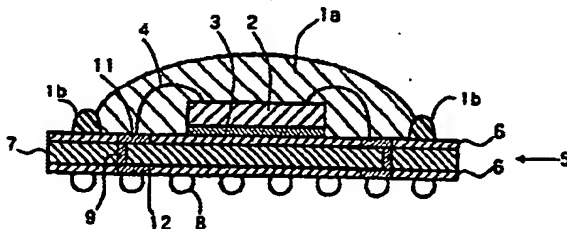
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(54) PASTE COMPOSITION, AND PROTECTIVE FILM AND SEMICONDUCTOR DEVICE BOTH OBTAINED WITH THE SAME

(57) A paste composition which comprises as essential ingredients (A) a thermoplastic resin, (B) an epoxy resin, (C) a coupling agent, (D) a powdery inorganic filler, (E) a powder having rubber elasticity and (F) an organic solvent and which, when applied and dried, gives a coating film having a void content of 3 % by volume or higher and a water vapor permeability as measured at 40°C and 90 %RH of 500 g/m²·24h or less; a

protective film which is formed by applying the paste composition to a surface of a semiconductor part and drying it and has a void content of 3 % by volume or higher and a water vapor permeability as measured at 40°C and 90 %RH of 500 g/m²·24h or less; and a semiconductor device having the protective film.

FIG. 1



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